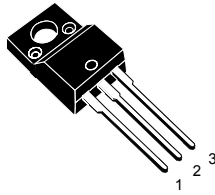
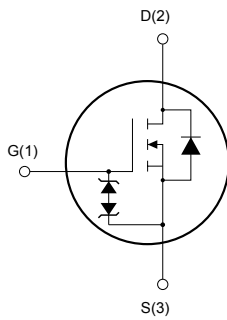


## N-channel 600 V, 0.255 $\Omega$ typ., 13 A MDmesh M2 Power MOSFET in a TO-220FP package



TO-220FP



AM15572v1\_no\_tab


**Product status link**
[STF18N60M2](#)
**Product summary**

<b>Order code</b>	STF18N60M2
<b>Marking</b>	18N60M2
<b>Package</b>	TO-220FP
<b>Packing</b>	Tube

### Features

Order code	$V_{DS} @ T_{Jmax}$	$R_{DS(on)}$ max.	$I_D$
STF18N60M2	650 V	0.280 $\Omega$	13 A

- Extremely low gate charge
- Excellent output capacitance ( $C_{OSS}$ ) profile
- 100% avalanche tested
- Zener-protected

### Applications

- Switching applications
- LCC converters
- Resonant converters

### Description

This device is an N-channel Power MOSFET developed using MDmesh M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	13	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	8	A
$I_{DM}^{(2)}$	Drain current (pulsed)	52	A
$P_{TOT}$	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	25	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(4)}$	MOSFET $dv/dt$ ruggedness	50	V/ns
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t = 1\text{ s}$ ; $T_C = 25\text{ }^\circ\text{C}$ )	2.5	kV
$T_{stg}$	Storage temperature range	-55 to 150	$^\circ\text{C}$
$T_j$	Operating junction temperature range		

- Limited by maximum junction temperature.
- Pulse width limited by safe operating area.
- $I_{SD} \leq 13\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ;  $V_{DS(peak)} < V_{(BR)DSS}$ ,  $V_{DD} = 400\text{ V}$
- $V_{DS} \leq 480\text{ V}$

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	5	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient	62.5	$^\circ\text{C}/\text{W}$

**Table 3. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{jmax}$ )	3	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	135	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified).

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}, V_{GS} = 0\text{ V}$	600			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V}, T_C = 125\text{ °C}^{(1)}$			100	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}, V_{GS} = \pm 25\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 6.5\text{ A}$		0.255	0.280	$\Omega$

1. Defined by design, not subject to production test.

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz}, V_{GS} = 0\text{ V}$	-	791	-	pF
$C_{oss}$	Output capacitance		-	40	-	pF
$C_{rSS}$	Reverse transfer capacitance		-	1.3	-	pF
$C_{oss\ eq.}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }480\text{ V}, V_{GS} = 0\text{ V}$	-	164.5	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}, I_D = 0\text{ A}$	-	5.6	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}, I_D = 13\text{ A}, V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 14. Test circuit for gate charge behavior)	-	21.5	-	nC
$Q_{gs}$	Gate-source charge		-	3.2	-	nC
$Q_{gd}$	Gate-drain charge		-	11.3	-	nC

1.  $C_{oss\ eq.}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}, I_D = 6.5\text{ A}, R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$ (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	12	-	ns
$t_r$	Rise time		-	9	-	ns
$t_{d(off)}$	Turn-off delay time		-	47	-	ns
$t_f$	Fall time		-	10.6	-	ns

**Table 7. Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		13	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		52	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 13\text{ A}$ , $V_{GS} = 0\text{ V}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 13\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$	-	305		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60\text{ V}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	3.3		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	22		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 13\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$	-	417		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$	-	4.6		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	22		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

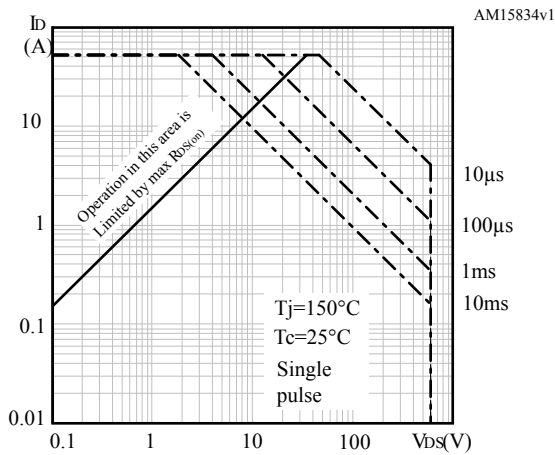


Figure 2. Thermal impedance

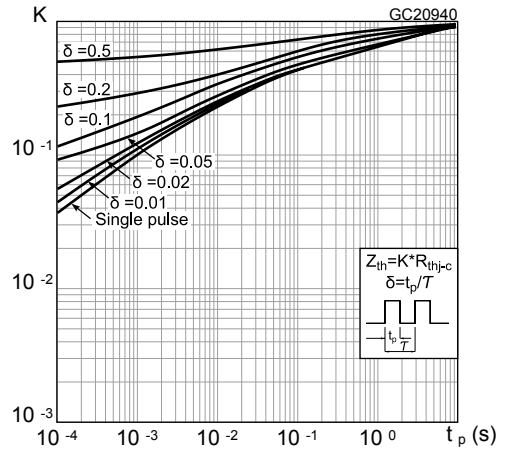


Figure 3. Output characteristics

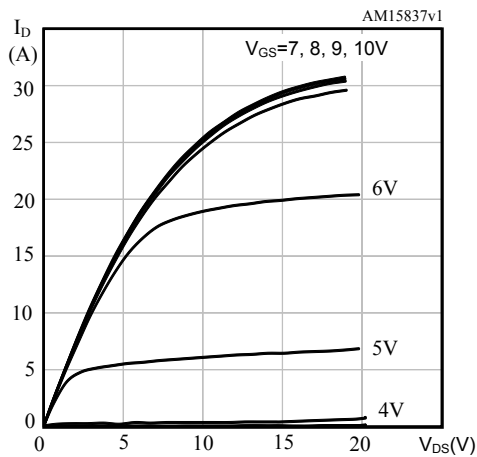


Figure 4. Transfer characteristics

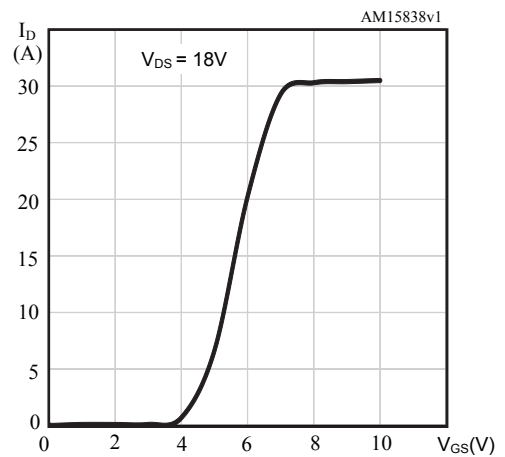


Figure 5. Gate charge vs gate-source voltage

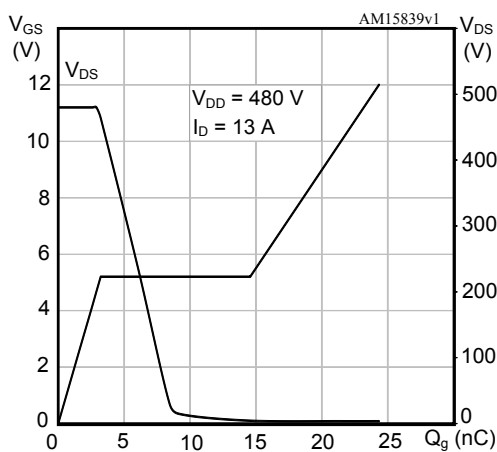


Figure 6. Static drain-source on-resistance

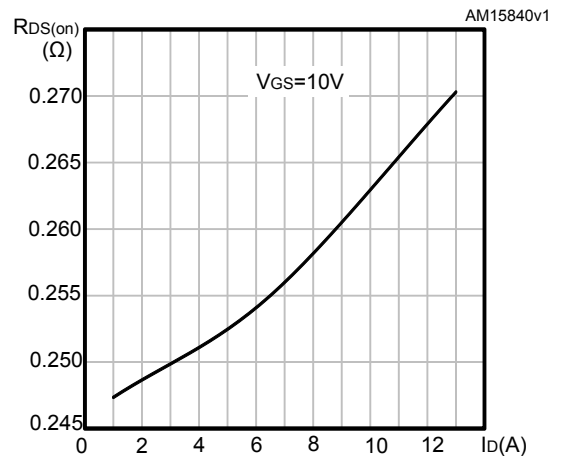


Figure 7. Capacitance variations

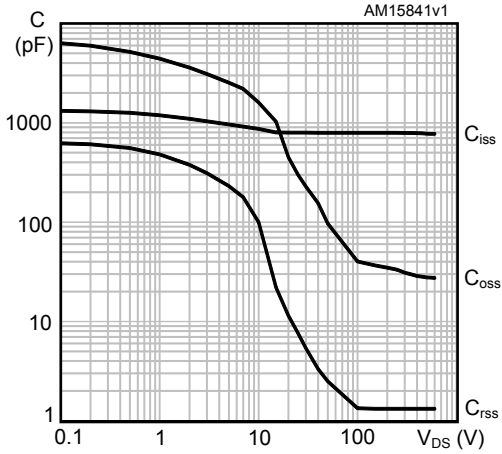


Figure 8. Normalized gate threshold voltage vs. temperature

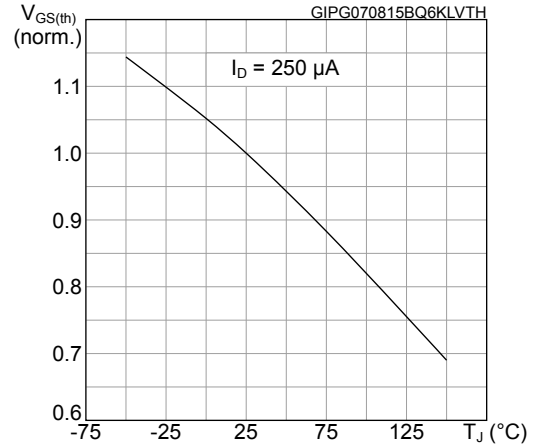


Figure 9. Normalized on-resistance vs temperature

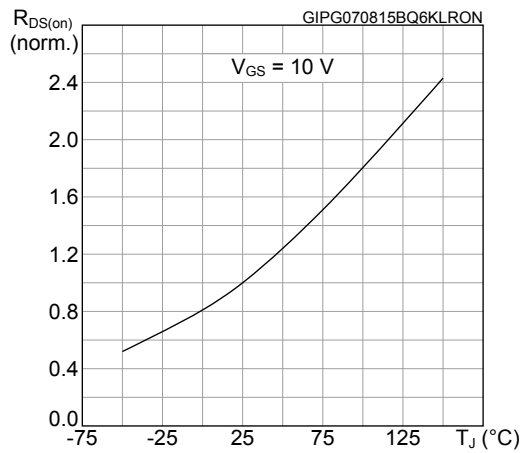


Figure 10. Source-drain diode forward characteristics

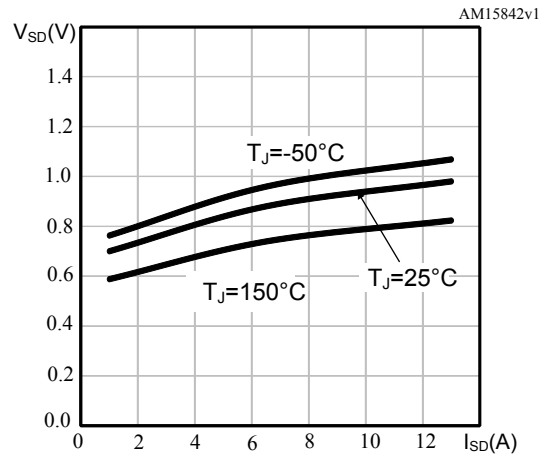


Figure 11. Normalized V<sub>(BR)DSS</sub> vs temperature

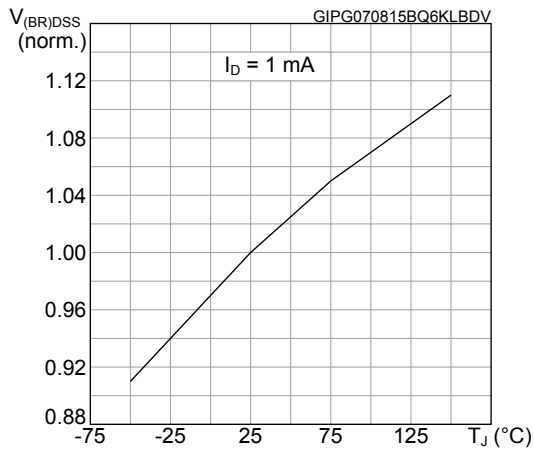
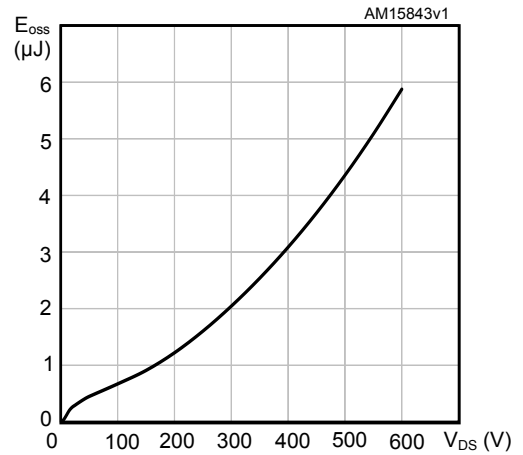
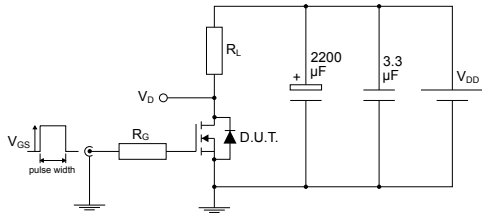


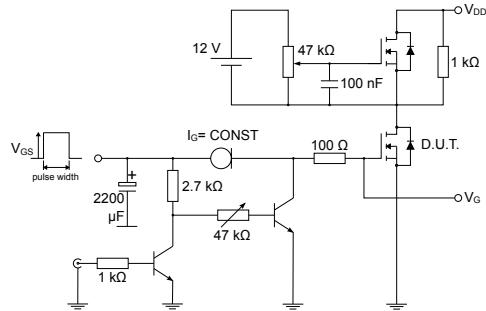
Figure 12. Output capacitance stored energy



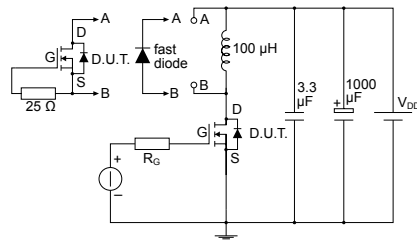
### 3 Test circuits

**Figure 13. Test circuit for resistive load switching times**


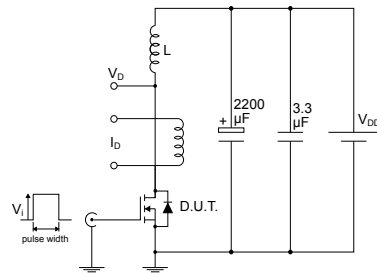
AM01468v1

**Figure 14. Test circuit for gate charge behavior**


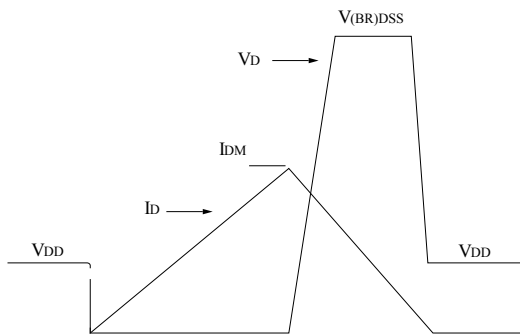
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**Figure 15. Test circuit for inductive load switching and diode recovery times**


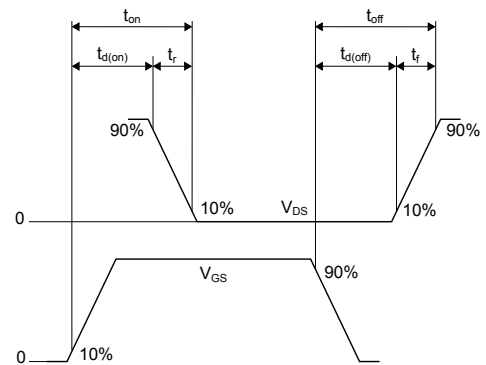
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**Figure 16. Unclamped inductive load test circuit**


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**Figure 17. Unclamped inductive waveform**


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**Figure 18. Switching time waveform**


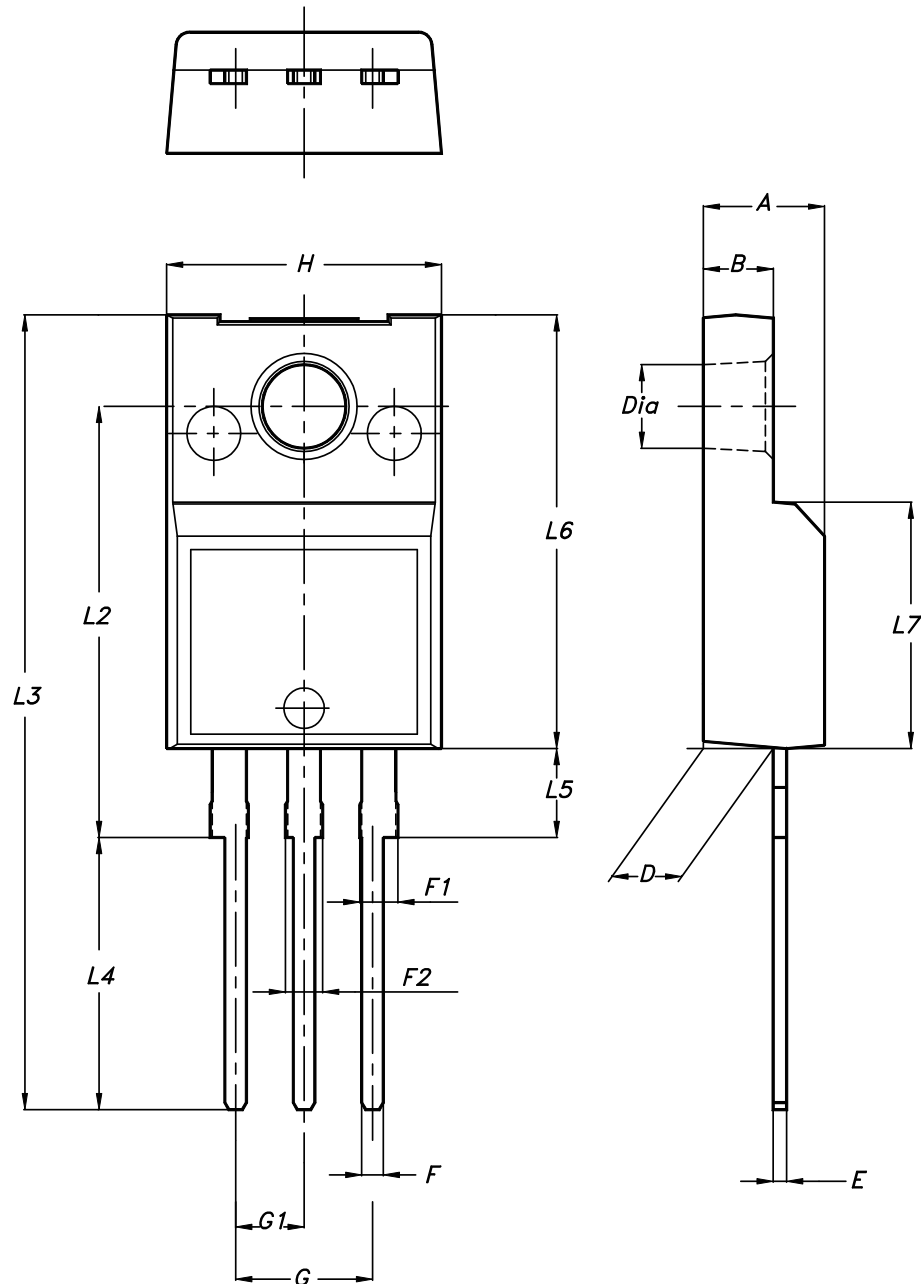
AM01473v1

## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 4.1 TO-220FP package information

Figure 19. TO-220FP package outline



7012510\_Rev\_13\_B



**Table 8. TO-220FP package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

## Revision history

**Table 9. Document revision history**

Date	Revision	Changes
04-Jun-2013	1	First release.
05-Jun-2013	2	<ul style="list-style-type: none"> <li>– Added: <i>note 2</i> in <i>Table 2</i></li> <li>– Modified: typical value for <math>C_{iss}</math>, <math>C_{oss\ eq.}</math>, <math>Q_g</math>, <math>Q_{gs}</math>, <math>Q_{gd}</math></li> <li>– Modified: <i>Figure 10</i> and <i>11</i></li> <li>– Minor text changes</li> </ul>
28-Feb-2014	3	<ul style="list-style-type: none"> <li>– Modified: <i>note 1</i> in <i>Table 2</i></li> <li>– <math>R_{thj-case}</math> value in <i>Table 3</i></li> <li>– Minor text changes</li> </ul>
19-Jun-2019	4	<p>Modified <a href="#">Figure 8. Normalized gate threshold voltage vs. temperature</a>, <a href="#">Figure 9. Normalized on-resistance vs temperature</a> and <a href="#">Figure 11. Normalized <math>V_{(BR)DSS}</math> vs temperature</a>.</p> <p>Minor text changes.</p>

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